

March 2015

# **FDD8647L**

# N-Channel PowerTrench<sup>®</sup> MOSFET 40 V, 42 A, 9 m $\Omega$

### **Features**

- Max  $r_{DS(on)} = 9 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 13 \text{ A}$
- Max  $r_{DS(on)}$  = 13 m $\Omega$  at  $V_{GS}$  = 4.5 V,  $I_D$  = 11 A
- Fast Switching
- 100% UIL tested
- RoHS Compliant

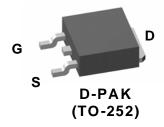


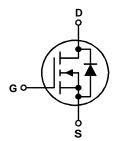
# **General Description**

This N-Channel MOSFET has been produced using Fairchild Semiconductor's proprietary PowerTrench technology to deliver low  $r_{DS(on)}$  and optimized BV<sub>DSS</sub> capability to offer superior performance benefit in the application.

# **Applications**

- Inverter
- Power Supplies





# MOSFET Maximum Ratings T<sub>C</sub> = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units	
$V_{DS}$	Drain to Source Voltage		40	V	
V <sub>GS</sub>	Gate to Source Voltage			±20	V
	Drain Current -Continuous (Package limited)	T <sub>C</sub> = 25 °C		42	
I <sub>D</sub>	-Continuous (Silicon limited) T <sub>C</sub> = 25 °C			52	
	-Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	14	Α
	-Pulsed			100	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	33	mJ
D	Power Dissipation	T <sub>C</sub> = 25 °C		43	W
$P_{D}$	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	3.1	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range			-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a	40	C/VV

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8647L	FDD8647L	D-PAK (TO-252)	13 "	16 mm	2500 units

# **Electrical Characteristics** $T_J = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40			V
$\frac{\Delta BV_{DS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		31		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 32 V, V <sub>GS</sub> = 0 V			1	μΑ
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		-6		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$		7.1	9.0	
r <sub>DS(on)</sub>	r <sub>DS(on)</sub> Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$		9.9	13.0	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}, T_J = 125 ^{\circ}\text{C}$		10.7	13.6	
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 13 \text{ A}$		49		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 20 V V 0 V	1230	1640	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	340	455	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 101112	55	80	pF
$R_g$	Gate Resistance		0.9		Ω

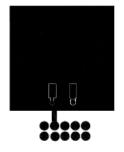
# **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		8	16	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 20 V, I <sub>D</sub> = 13 A,	3	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	19	34	ns
t <sub>f</sub>	Fall Time		2	10	ns
$Q_g$	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V	20	28	nC
Qg	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 20 \text{ V}$ ,	10	14	nC
Q <sub>gs</sub>	Gate to Source Charge	I <sub>D</sub> = 13 A	3.8		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		3.1		nC

## **Drain-Source Diode Characteristics**

V <sub>SD</sub> Source to Drain Diode Forward Voltage	Course to Drain Diado, Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.6 \text{ A}$ (Note 2)		0.75	1.2	
	$V_{GS} = 0 \text{ V}, I_S = 13 \text{ A}$ (Note 2)		0.84	1.3	v	
t <sub>rr</sub>	Reverse Recovery Time	- I <sub>F</sub> = 13 A, di/dt = 100 A/μs		28	45	ns
Q <sub>rr</sub>	Reverse Recovery Charge			15	27	nC

Tables. It R<sub>9JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>9JC</sub> is guaranteed by design while R<sub>9JA</sub> is determined by the user's board design.



a) 40 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 96 °C/W when mounted on a minimum pad

- 2: Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0%. 3: Starting T  $_J$  = 25 °C, L = 0.3 mH, I  $_{AS}$  = 15.0 A, V  $_{DD}$  = 36 V, V  $_{GS}$  = 10.0 V.

# Typical Characteristics $T_J = 25$ °C unless otherwise noted

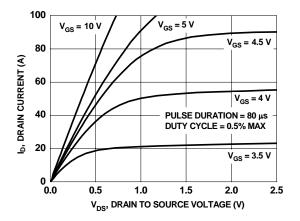


Figure 1. On Region Characteristics

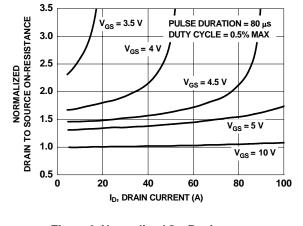


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

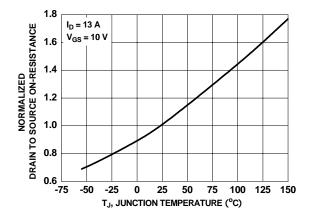


Figure 3. Normalized On Resistance vs Junction Temperature

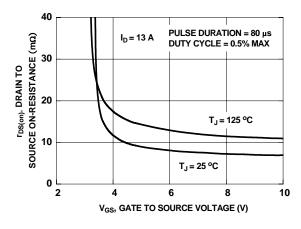


Figure 4. On-Resistance vs Gate to Source Voltage

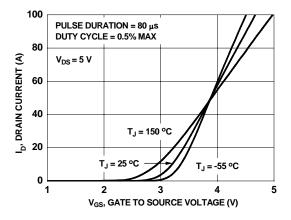


Figure 5. Transfer Characteristics

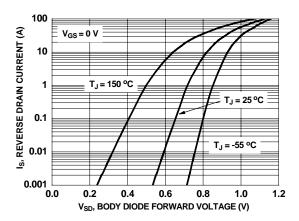


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

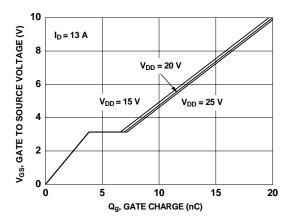


Figure 7. Gate Charge Characteristics

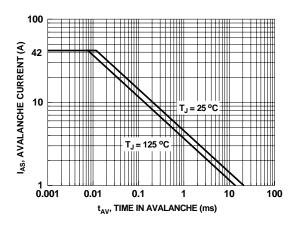


Figure 9. Unclamped Inductive Switching Capability

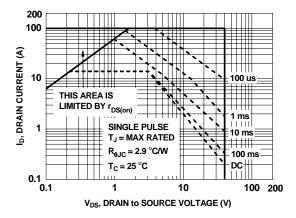


Figure 11. Forward Bias Safe Operating Area

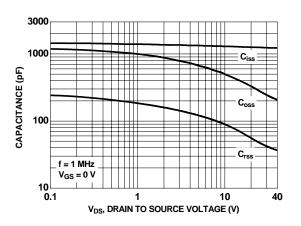


Figure 8. Capacitance vs Drain to Source Voltage

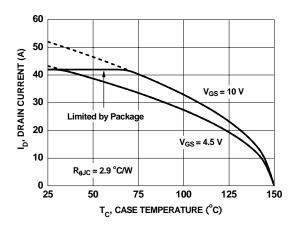


Figure 10. Maximum Continuous Drain Current vs Case Temperature

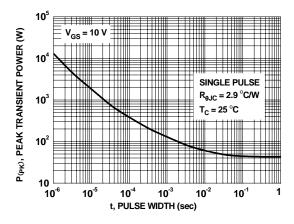


Figure 12. Single Pulse Maximum Power Dissipation

# **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

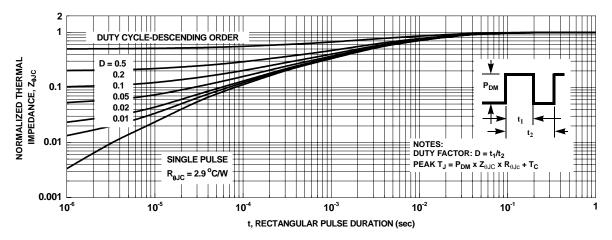


Figure 13. Junction-to-Case Transient Thermal Response Curve

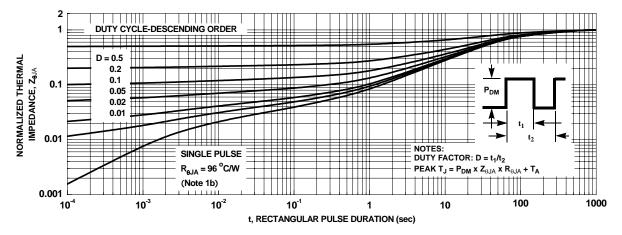


Figure 14. Junction-to-Ambient Transient Thermal Response Curve







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